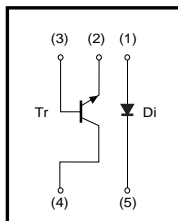


# Low-frequency transistor (isolated transistor and diode) UML2N

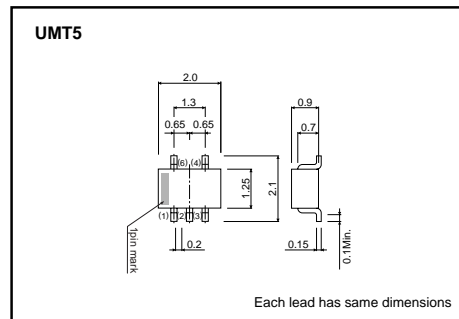
## ●Features

- 1) The 2SC2412K and a diode are housed independently in a UMT package.

## ●Equivalent circuit



## ●External dimensions (Unit : mm)



## ●Packaging specifications

Part No.	UML2N
Package	UMT5
Marking	L2
Code	TR
Basic ordering unit (pieces)	3000

## ●Absolute maximum ratings (Ta=25°C)

### Tr

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	60	V
Collector-emitter voltage	V <sub>CE0</sub>	50	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>c</sub>	0.15	A
Collector power dissipation	P <sub>c</sub>	0.15	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### Di

Parameter	Symbol	Limits	Unit
DC reverse voltage	V <sub>R</sub>	80	V
Peak reverse voltage	V <sub>RM</sub>	80	V
Mean rectifying current	I <sub>o</sub>	0.1	A
Peak forward voltage	I <sub>FM</sub>	0.3	A
Surge current	I <sub>surge</sub>	4	A
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C
Specified I/O frequencies	f	100	MHz

Transistors

●Electrical characteristics (Ta=25°C)

Tr

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	$BV_{CEO}$	50	–	–	V	$I_C=1mA$
Collector-base breakdown voltage	$BV_{CBO}$	60	–	–	V	$I_C=50\mu A$
Emitter-base breakdown voltage	$BV_{EBO}$	6	–	–	V	$I_E=50\mu A$
Collector cutoff current	$I_{CBO}$	–	–	0.1	$\mu A$	$V_{CB}=60V$
Emitter cutoff current	$I_{EBO}$	–	–	0.1	$\mu A$	$V_{EB}=5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	0.4	V	$I_C/I_B=50mA/5mA$
DC current transfer ratio	$h_{FE}$	120	–	560	–	$V_{CE}=6V, I_C=1mA$
Transition frequency	$f_T$	–	180	–	MHz	$V_{CE}=12V, I_E=-2mA, f=100MHz$
Output capacitance	$C_{ob}$	–	2	3.5	pF	$V_{CB}=12V, I_E=0A, f=1MHz$

Di

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	–	–	1.2	V	$I_F=100mA$
Reverse current	$I_R$	–	–	0.1	$\mu A$	$V_R=70V$
Capacitance between terminals	$C_T$	–	–	3.5	pF	$V_R=6V, f=1MHz$
Reverse recovery time	$t_{rr}$	–	–	4	ns	$V_R=6V, I_F=5mA, R_L=50\Omega$

●Electrical characteristic curves

Tr

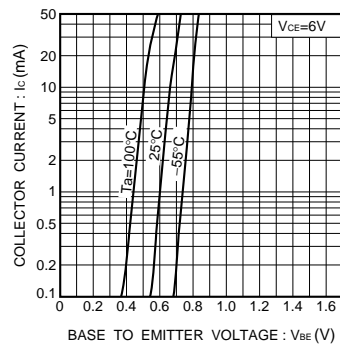


Fig.1 Grounded emitter propagation characteristics

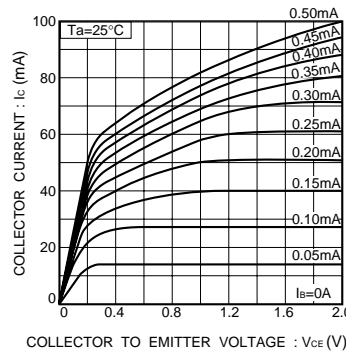


Fig.2 Grounded emitter output characteristics ( I )

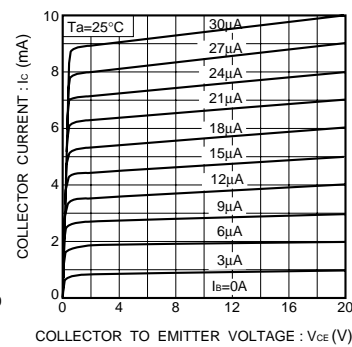


Fig.3 Grounded emitter output characteristics ( II )

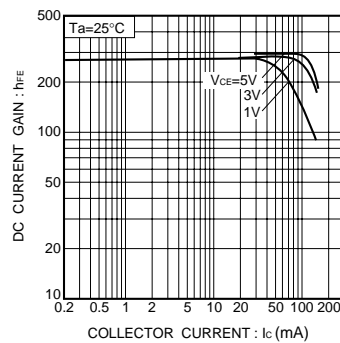


Fig.4 DC current gain vs. collector current ( I )

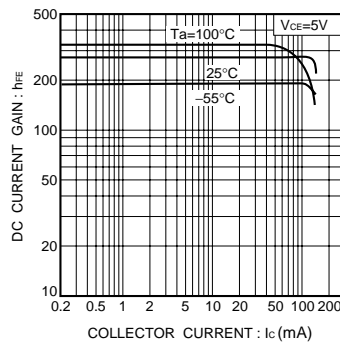


Fig.5 DC current gain vs. collector current ( II )

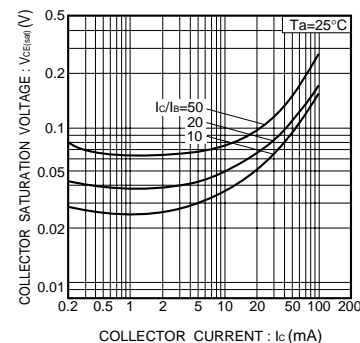


Fig. 6 Collector-emitter saturation voltage vs. collector current

Transistors

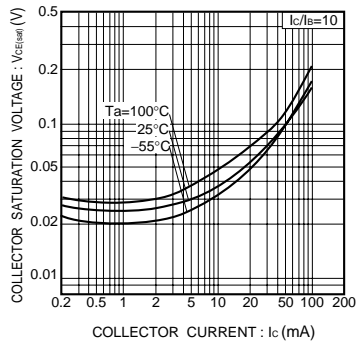


Fig.7 Collector-emitter saturation voltage vs. collector current ( I )

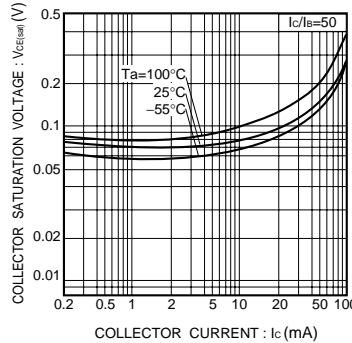


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

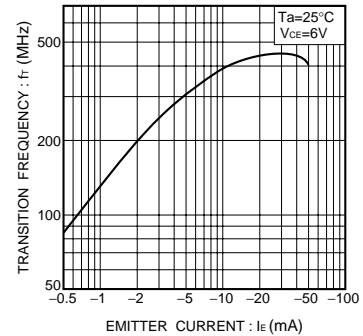


Fig.9 Gain bandwidth product vs. emitter current

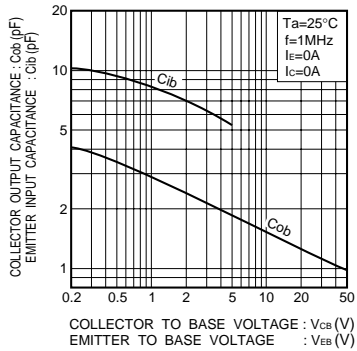


Fig.10 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

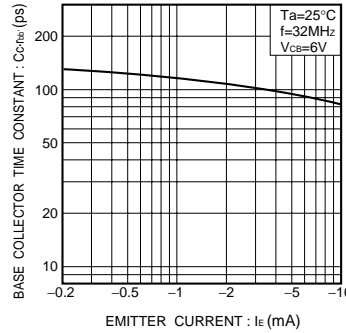


Fig.11 Base-collector time constant vs. emitter current

Di

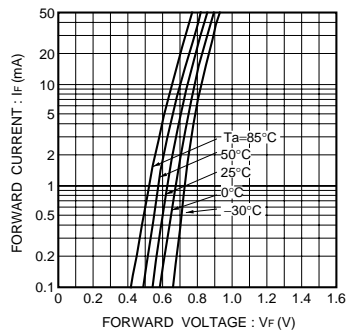


Fig.12 Forward characteristics

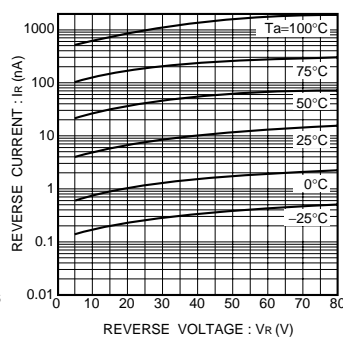


Fig.13 Reverse characteristics

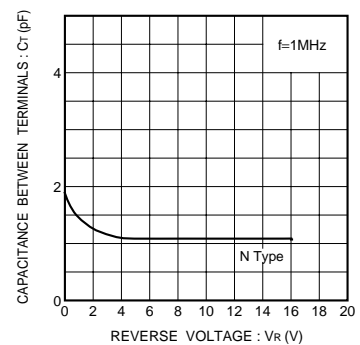


Fig.14 Capacitance between terminals characteristics

Transistors

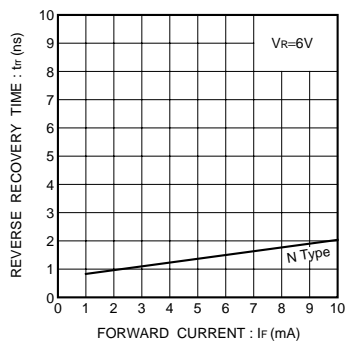


Fig.15 Reverse recovery time

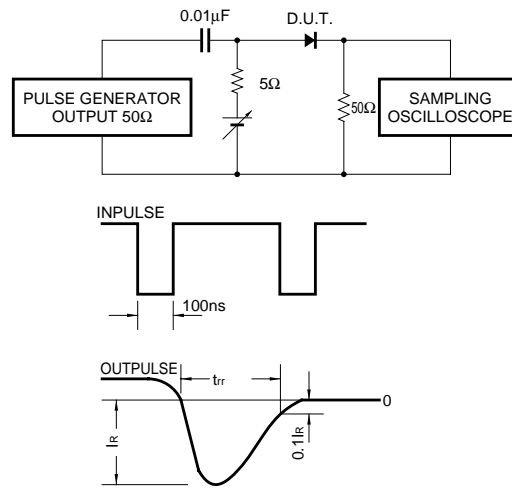


Fig.16 Reverse recovery time ( $t_{rr}$ ) measurement circuit

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